

Explicitly correlated six-dimensional potential energy surface for the SiCSi+H₂ complex (Supplementary materials)

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3.1.2 Features of the surface

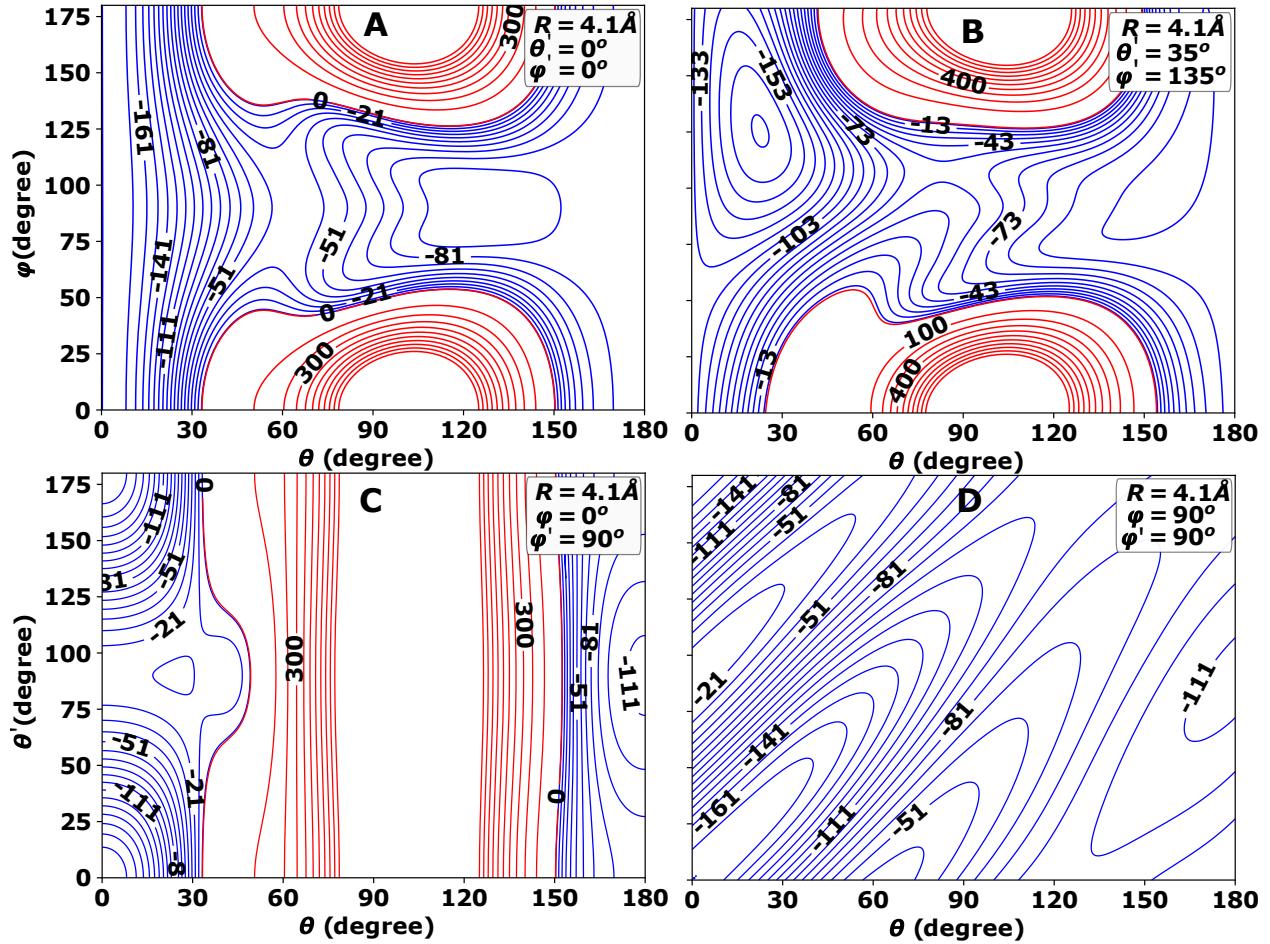


Figure 1: Contour plots of the PES at different angular configurations for $\gamma = \gamma_e$. Negative (blue lines) and positive (red lines) energies are separated in steps of 10 cm^{-1} and 100 cm^{-1} , respectively.

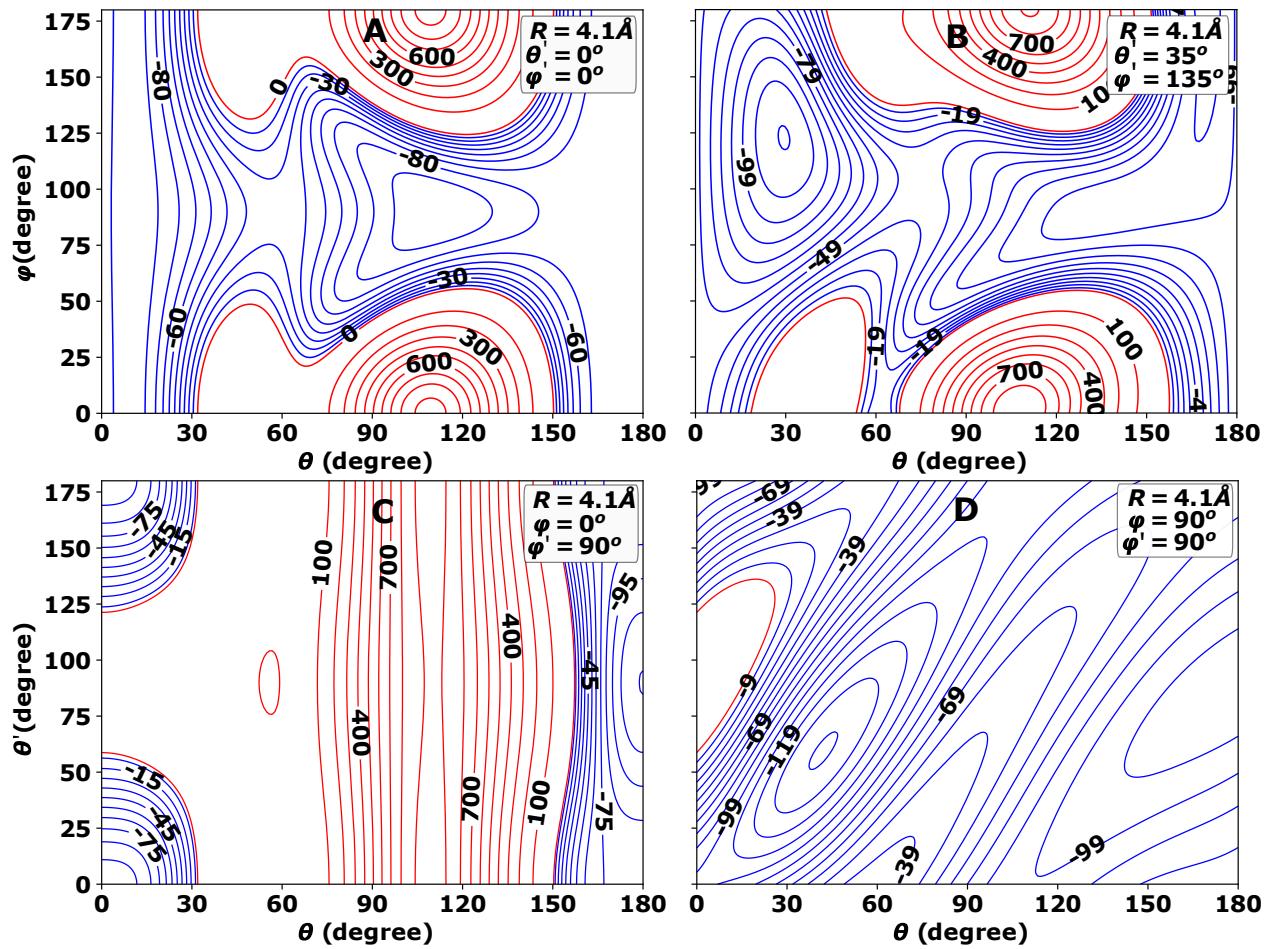


Figure 2: Same as Fig. 1 but for $\gamma = 80^\circ$.

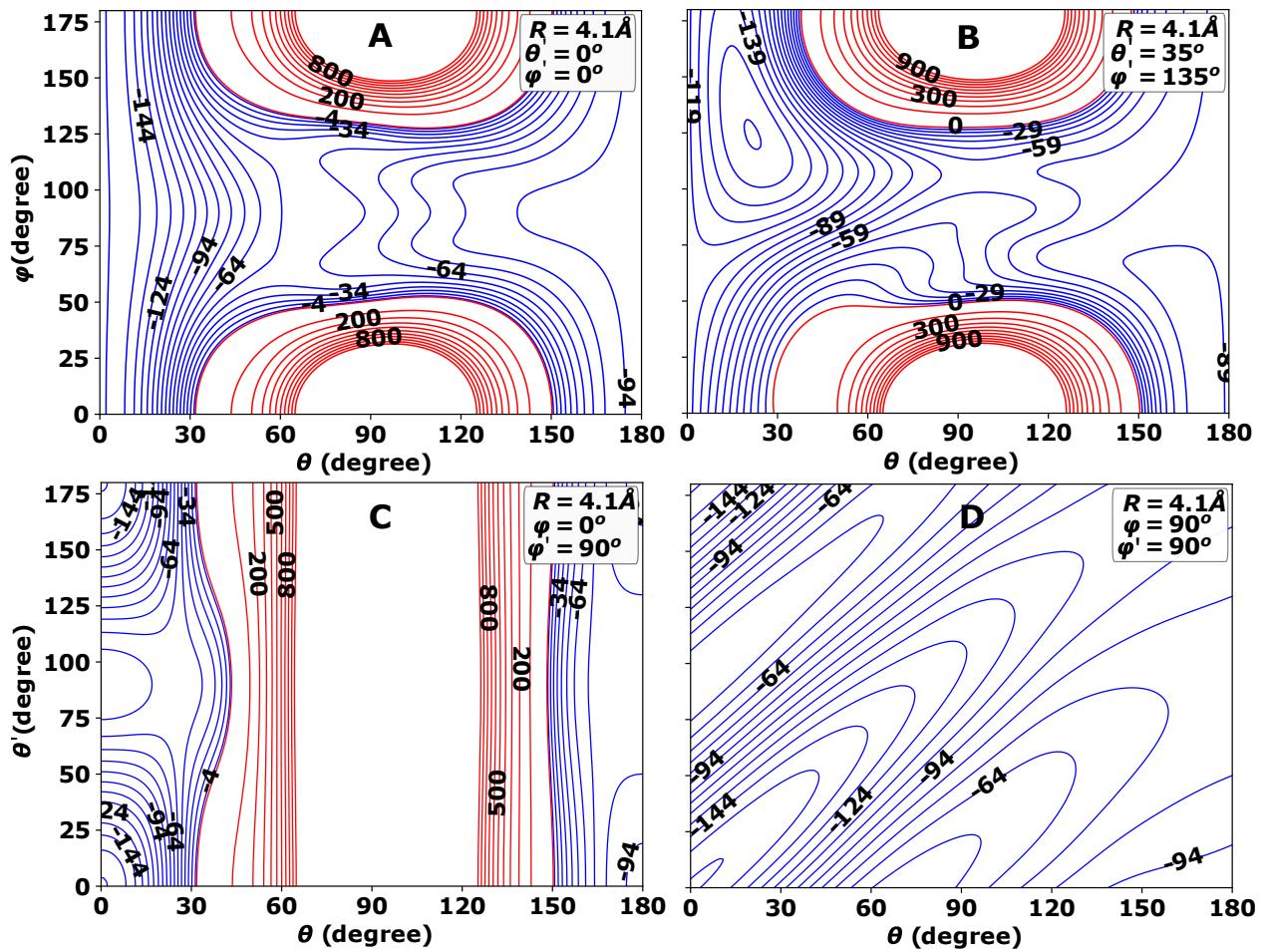


Figure 3: Same as Fig. 1 but for $\gamma = 150^\circ$.

3.1.3 Long range behavior

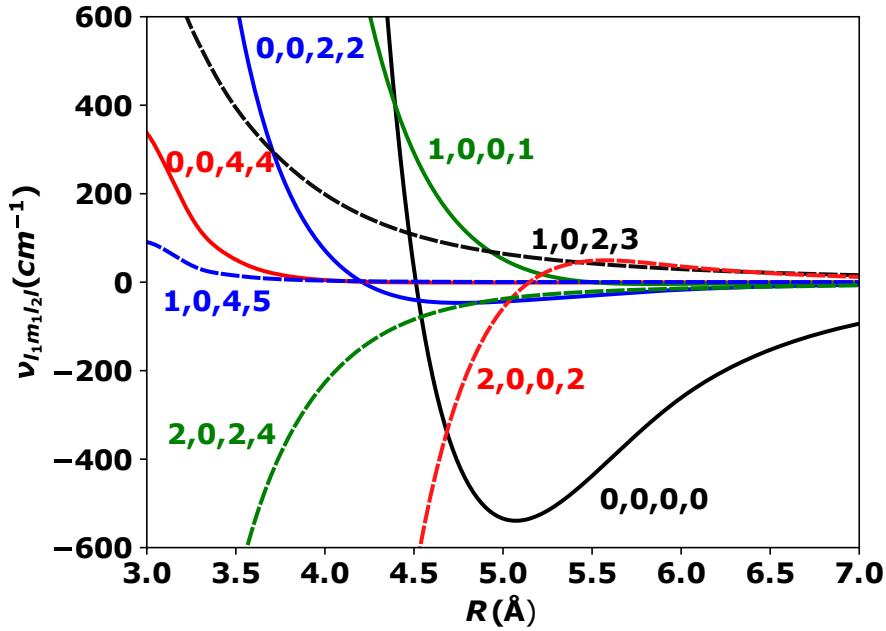


Figure 4: First $v_{l_1 m_1 l_2 l}(\gamma_e, R)$ radial coefficients of the SiCSi-H₂ PES.

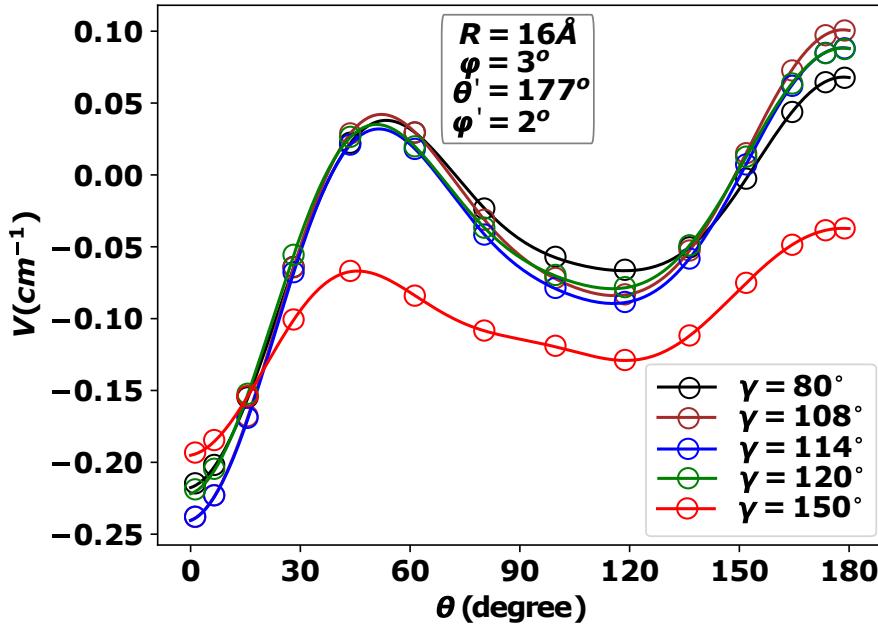


Figure 5: Analytical (lines) and *ab initio* (points) energies of the SiCSi-H₂ complex at $R = 16$ Å for several values of γ , at a fixed configuration of φ , θ' and φ' . These *ab initio* energies were not included in the fitting procedure.

3.2 Averaged four-dimensional PES

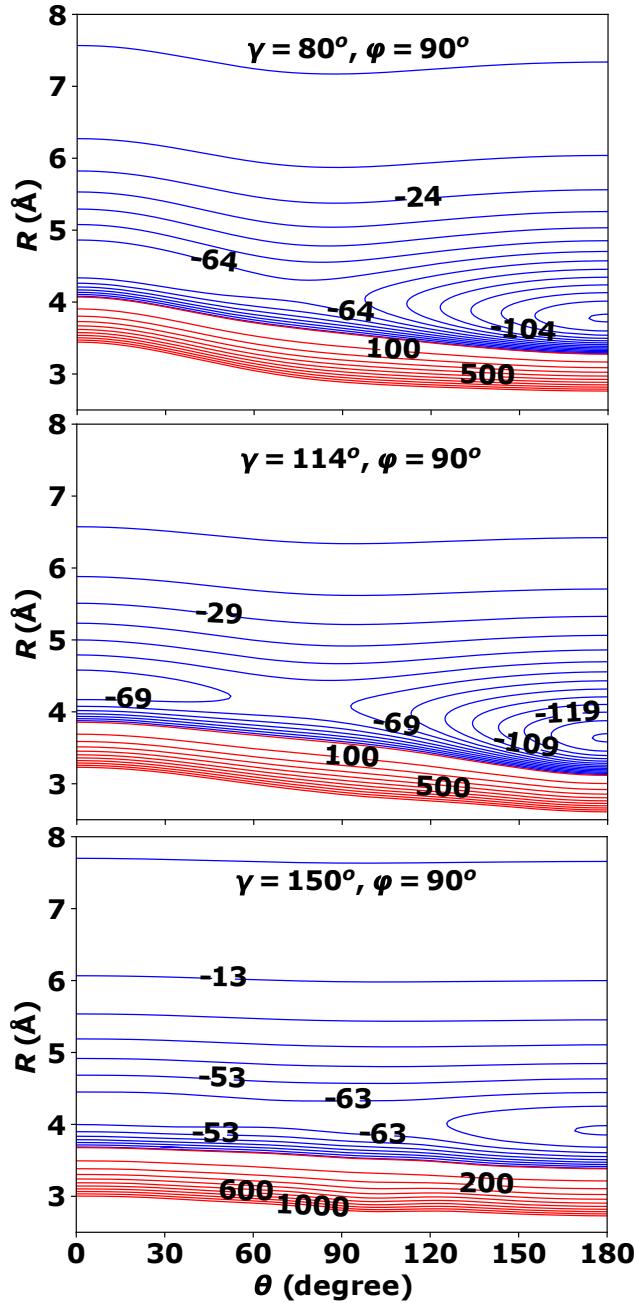


Figure 6: Contour plots of the PES of SiCSi-H₂ averaged over the H₂ orientation for $\varphi = 90^\circ$ at several values of γ . Negative (blue lines) and positive (red lines) energies are separated in steps of 6 cm⁻¹ and 50 cm⁻¹, respectively.